

X4 SRAM Nonvolatile Controller Unit

Features

- Power monitoring and switching for 3-volt battery-backup applications
- Write-protect control
- 2-input decoder for control of up to 4 banks of SRAM
- 3-volt primary cell inputs
- Less than 10ns chip-enable propagation delay
- 5% or 10% supply operation

General Description

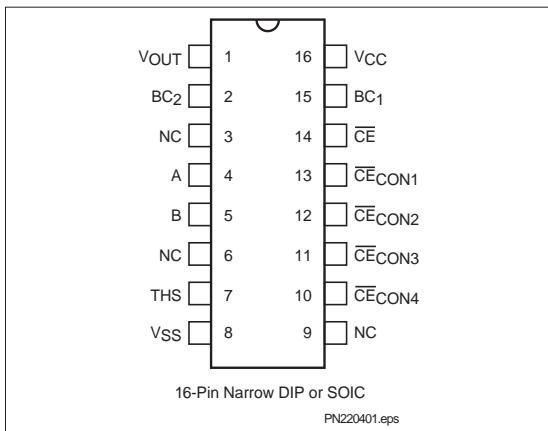
The CMOS bq2204A SRAM Nonvolatile Controller Unit provides all necessary functions for converting up to four banks of standard CMOS SRAM into nonvolatile read/write memory.

A precision comparator monitors the 5V VCC input for an out-of-tolerance condition. When out-of-tolerance is detected, the four conditioned chip-enable outputs are forced inactive to write-protect up to four banks of SRAM.

During a power failure, the external SRAMs are switched from the VCC supply to one of two 3V backup supplies. On a subsequent power-up, the SRAMs are write-protected until a power-valid condition exists.

During power-valid operation, a two-input decoder transparently selects one of up to four banks of SRAM.

Pin Connections



Pin Names

| | |
|---------------|-----------------------------------|
| VOUT | Supply output |
| BC1-BC2 | 3 volt primary backup cell inputs |
| THS | Threshold select input |
| CE | chip-enable active low input |
| CECON1-CECON4 | Conditioned chip-enable outputs |
| A-B | Decoder inputs |
| NC | No connect |
| VCC | +5 volt supply input |
| VSS | Ground |

Functional Description

Up to four banks of CMOS static RAM can be battery-backed using the VOUT and conditioned chip-enable output pins from the bq2204A. As VCC slews down during a power failure, the conditioned chip-enable outputs CECON1 through CECON4 are forced inactive independent of the chip-enable input CE.

This activity unconditionally write-protects the external SRAM as VCC falls below an out-of-tolerance threshold VPFD. VPFD is selected by the threshold select input pin, THS. If THS is tied to VSS, the power-fail detection occurs at 4.62V typical for 5% supply operation.

If THS is tied to VCC, power-fail detection occurs at 4.37V typical for 10% supply operation. The THS pin must be tied to VSS or VCC for proper operation.

If a memory access is in process to any of the four external banks of SRAM during power-fail detection, that memory cycle continues to completion before the memory is write-protected. If the memory cycle is not terminated within time tWPt, all four chip-enable outputs are unconditionally driven high, write-protecting the controlled SRAMs.

bq2204A

As the supply continues to fall past VPFD, an internal switching device forces VOUT to one of the two external backup energy sources. $\overline{CECON1}$ through $\overline{CECON4}$ are held high by the VOUT energy source.

During power-up, VOUT is switched back to the 5V supply as VCC rises above the backup cell input voltage sourcing VOUT. Outputs $\overline{CECON1}$ through $\overline{CECON4}$ are held inactive for time tCER (120ms maximum) after the power supply has reached VPFD, independent of the CE input, to allow for processor stabilization.

During power-valid operation, the \overline{CE} input is passed through to one of the four \overline{CECON} outputs with a propagation delay of less than 10ns. The \overline{CE} input is output on one of the four \overline{CECON} output pins depending on the level of the decode inputs at A and B as shown in the Truth Table.

The A and B inputs are usually tied to high-order address pins so that a large nonvolatile memory can be designed using lower-density memory devices. Nonvolatility and decoding are achieved by hardware hookup as shown in Figure 1.

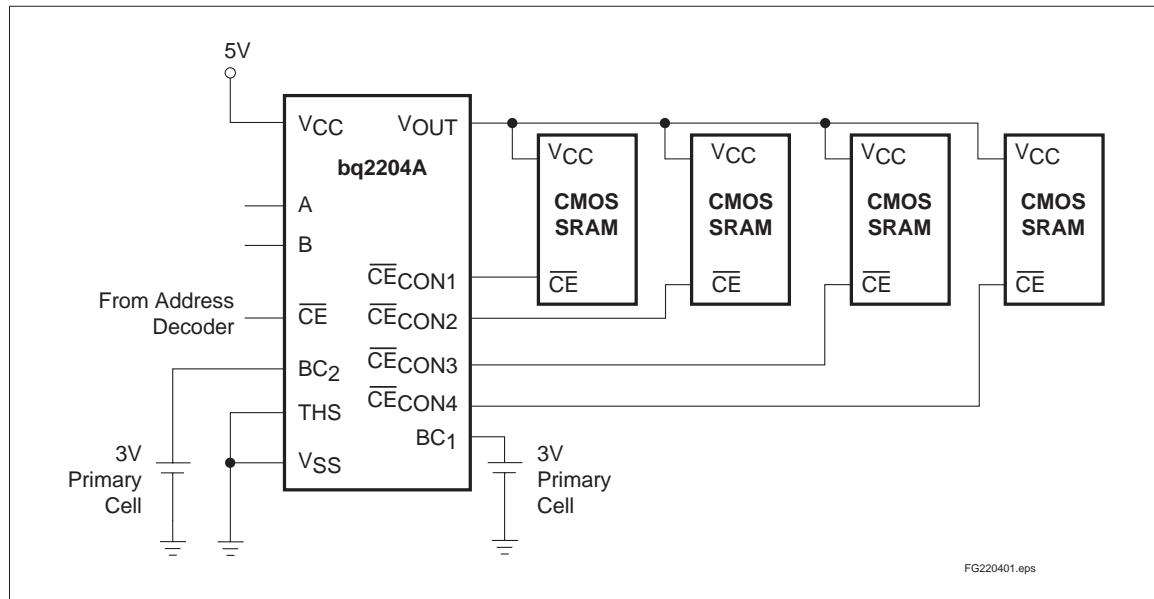


Figure 1. Hardware Hookup (5% Supply Operation)

Energy Cell Inputs—BC₁, BC₂

Two backup energy source inputs are provided on the bq2204A. The BC₁ and BC₂ inputs accept a 3V primary battery (non-rechargeable), typically some type of lithium chemistry. If no primary cell is to be used on either BC₁ or BC₂, the unused input should be tied to V_{SS}.

V_{CC} falling below V_{PF} starts the comparison of BC₁ and BC₂. The BC input comparison continues until V_{CC} rises above V_{SO}. Power to V_{OUT} begins with BC₁ and switches to BC₂ only when V_{BC1} is less than V_{BC2} minus V_{BSO}. The controller alternates to the higher BC voltage only when the difference between the BC input voltages is greater than V_{BSO}. Alternating the backup batteries allows one-at-a-time battery replacement and efficient use of both backup batteries.

To prevent battery drain when there is no valid data to retain, V_{OUT} and $\overline{CECON1-4}$ are internally isolated from BC₁ and BC₂ by either of the following conditions:

- Initial connection of a battery to BC₁ or BC₂, or
- Presentation of an isolation signal on \overline{CE} .

A valid isolation signal requires \overline{CE} low as V_{CC} crosses both V_{PF} and V_{SO} during a power-down. See Figure 2. Between these two points in time, \overline{CE} must be brought to the point of (0.48 to 0.52)*V_{CC} and held for at least 700ns. The isolation signal is invalid if \overline{CE} exceeds 0.54*V_{CC} at any point between V_{CC} crossing V_{PF} and V_{SO}.

The appropriate battery is connected to V_{OUT} and $\overline{CECON1-4}$ immediately on subsequent application and removal of V_{CC}.

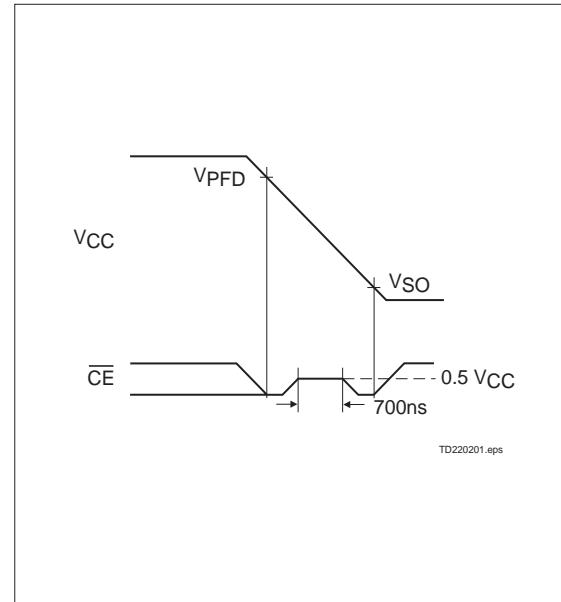


Figure 2. Battery Isolation Signal

Truth Table

| Input | | | Output | | | |
|-----------------|---|---|---------------------|---------------------|---------------------|---------------------|
| \overline{CE} | A | B | $\overline{CECON1}$ | $\overline{CECON2}$ | $\overline{CECON3}$ | $\overline{CECON4}$ |
| H | X | X | H | H | H | H |
| L | L | L | L | H | H | H |
| L | H | L | H | L | H | H |
| L | L | H | H | H | L | H |
| L | H | H | H | H | H | L |

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Absolute Maximum Ratings

| Symbol | Parameter | Value | Unit | Conditions |
|---------|---|--------------|------|---------------------|
| VCC | DC voltage applied on VCC relative to VSS | -0.3 to +7.0 | V | |
| VT | DC voltage applied on any pin excluding VCC relative to VSS | -0.3 to +7.0 | V | $VT \leq VCC + 0.3$ |
| TOPR | Operating temperature | 0 to 70 | °C | Commercial |
| | | -40 to +85 | °C | Industrial "N" |
| TSTG | Storage temperature | -55 to +125 | °C | |
| TBIAS | Temperature under bias | -40 to +85 | °C | |
| TSOLDER | Soldering temperature | 260 | °C | For 10 seconds |
| IOUT | VOUT current | 200 | mA | |

Note: Permanent device damage may occur if **Absolute Maximum Ratings** are exceeded. Functional operation should be limited to the Recommended DC Operating Conditions detailed in this data sheet. Exposure to conditions beyond the operational limits for extended periods of time may affect device reliability.

Recommended DC Operating Conditions (TA = TOPR)

| Symbol | Parameter | Minimum | Typical | Maximum | Unit | Notes |
|---------------|---------------------|---------|---------|-------------|------|-------------|
| VCC | Supply voltage | 4.75 | 5.0 | 5.5 | V | THS = VSS |
| | | 4.50 | 5.0 | 5.5 | V | THS = VCC |
| VSS | Supply voltage | 0 | 0 | 0 | V | |
| VIL | Input low voltage | -0.3 | - | 0.8 | V | |
| VIH | Input high voltage | 2.2 | - | $VCC + 0.3$ | V | |
| VBC1, VBC2 | Backup cell voltage | 2.0 | - | 4.0 | V | $VCC < VBC$ |
| THS | Threshold select | -0.3 | - | $VCC + 0.3$ | V | |

Note: Typical values indicate operation at $TA = 25^{\circ}\text{C}$, $VCC = 5\text{V}$ or VBC .

DC Electrical Characteristics (TA = TOPR, VCC = 5V ± 10%)

| Symbol | Parameter | Minimum | Typical | Maximum | Unit | Conditions/Notes |
|-----------------------------|-----------------------------|-----------------------|------------------|---------|------|--|
| IL _I | Input leakage current | - | - | ± 1 | µA | V _{IN} = V _{SS} to V _{CC} |
| V _{OH} | Output high voltage | 2.4 | - | - | V | I _{OH} = -2.0mA |
| V _{OHB} | V _{OH} , BC supply | V _{BC} - 0.3 | - | - | V | V _{BC} > V _{CC} , I _{OH} = -10µA |
| V _{OL} | Output low voltage | - | - | 0.4 | V | I _{OL} = 4.0mA |
| I _{CC} | Operating supply current | - | 3 | 6 | mA | No load on outputs. |
| V _{PF} D | Power-fail detect voltage | 4.55 | 4.62 | 4.75 | V | THS = V _{SS} |
| | | 4.30 | 4.37 | 4.50 | V | THS = V _{CC} |
| V _{SO} | Supply switch-over voltage | - | V _{BC} | - | V | |
| I _{CCDR} | Data-retention mode current | - | - | 100 | nA | V _{OUT} data-retention current to additional memory not included. |
| V _{BC} | Active backup cell voltage | - | V _{BC1} | - | V | V _{BC1} > V _{BC2} + V _{B_{SO}} |
| | | - | V _{BC2} | - | V | V _{BC2} > V _{BC1} + V _{B_{SO}} |
| V _{B_{SO}} | Battery switch-over voltage | 0.25 | 0.4 | 0.6 | V | |
| I _{OUT1} | V _{OUT} current | - | - | 160 | mA | V _{OUT} > V _{CC} - 0.3V |
| I _{OUT2} | V _{OUT} current | - | 100 | - | µA | V _{OUT} > V _{BC} - 0.2V |

Note: Typical values indicate operation at TA = 25°C, V_{CC} = 5V or V_{BC}.

Capacitance (TA = 25°C, F = 1MHz, V_{CC} = 5.0V)

| Symbol | Parameter | Minimum | Typical | Maximum | Unit | Conditions |
|------------------|--------------------|---------|---------|---------|------|---------------------|
| C _{IN} | Input capacitance | - | - | 8 | pF | Input voltage = 0V |
| C _{OUT} | Output capacitance | - | - | 10 | pF | Output voltage = 0V |

Note: This parameter is sampled and not 100% tested.

bq2204A

AC Test Conditions

| Parameter | Test Conditions |
|--|-----------------------------------|
| Input pulse levels | 0V to 3.0V |
| Input rise and fall times | 5ns |
| Input and output timing reference levels | 1.5V (unless otherwise specified) |

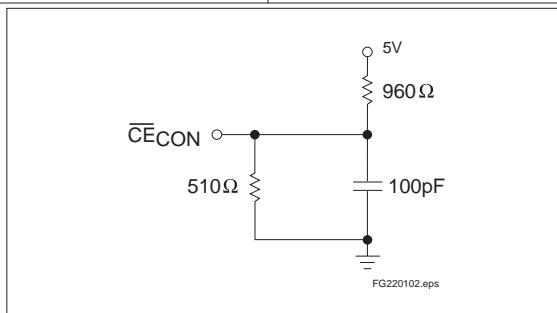


Figure 3. Output Load

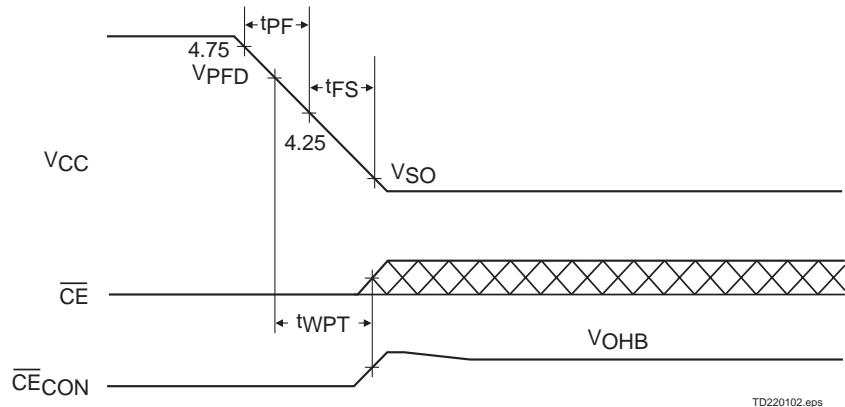
Power-Fail Control ($T_A = TOPR$)

| Symbol | Parameter | Minimum | Typical | Maximum | Unit | Notes |
|--------|-------------------------------|---------|---------|---------|------|--|
| tPF | VCC slew, 4.75V to 4.25V | 300 | - | - | μs | |
| tFS | VCC slew, 4.25V to VSO | 10 | - | - | μs | |
| tPU | VCC slew, 4.25V to 4.75V | 0 | - | - | μs | |
| tCED | chip-enable propagation delay | - | 7 | 10 | ns | |
| tAS | A,B set up to \overline{CE} | 0 | - | - | ns | |
| tCER | chip-enable recovery | 40 | 80 | 120 | ms | Time during which SRAM is write-protected after VCC passes VPFD on power-up. |
| tWPT | Write-protect time | 40 | 100 | 150 | μs | Delay after VCC slews down past VPFD before SRAM is write-protected. |

Note: Typical values indicate operation at $T_A = 25^\circ\text{C}$, $VCC = 5\text{V}$.

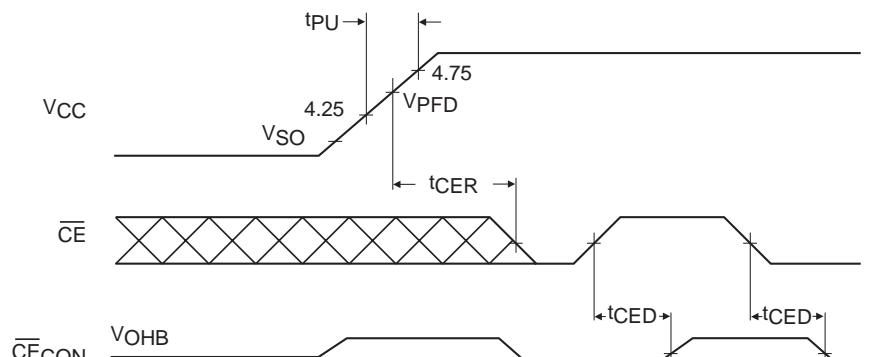
Caution: Negative undershoots below the absolute maximum rating of **-0.3V** in battery-backup mode may affect data integrity.

Power-Down Timing



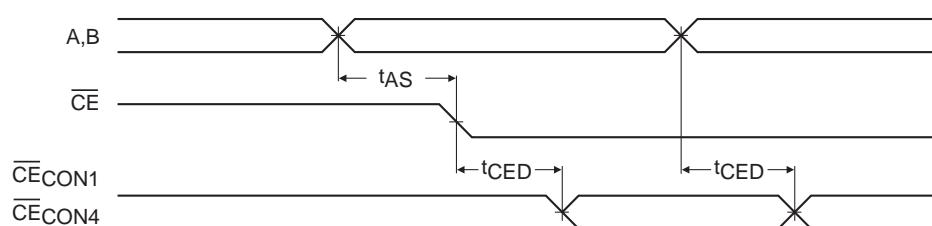
TD220102.eps

Power-Up Timing



TD220103.eps

Address-Decode Timing



TD220402.eps

bq2204A

Data Sheet Revision History

| Change No. | Page No. | Description of Change | Nature of Change |
|------------|----------|---|------------------|
| 1 | All | bq2204A replaces bq2204. | |
| 1 | 1, 4-5 | 10% tolerance requires the THS pin to be tied to VCC, not VOUT. | |
| 1 | 3 | Energy cell input selection process alternates between BC1 and BC2. | |

Note: Change 1 = Dec. 1992 changes from Sept. 1991

Dec. 1992 B

PACKAGING INFORMATION

| Orderable part number | Status (1) | Material type (2) | Package Pins | Package qty Carrier | RoHS (3) | Lead finish/ Ball material (4) | MSL rating/ Peak reflow (5) | Op temp (°C) | Part marking (6) |
|-----------------------------|---------------|----------------------|----------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| BQ2204APN | Active | Production | PDIP (N) 16 | 25 TUBE | Yes | NIPDAU | N/A for Pkg Type | 0 to 70 | 2204APN |
| BQ2204APN.B | Active | Production | PDIP (N) 16 | 25 TUBE | Yes | NIPDAU | N/A for Pkg Type | 0 to 70 | 2204APN |
| BQ2204ASN | Active | Production | SOIC (D) 16 | 40 TUBE | Yes | NIPDAU | Level-2-260C-1 YEAR | 0 to 70 | 2204A |
| BQ2204ASN-N | Active | Production | SOIC (D) 16 | 40 TUBE | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | 2204A |
| BQ2204ASN-N.B | Active | Production | SOIC (D) 16 | 40 TUBE | Yes | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | 2204A |
| BQ2204ASN.B | Active | Production | SOIC (D) 16 | 40 TUBE | Yes | NIPDAU | Level-2-260C-1 YEAR | 0 to 70 | 2204A |
| BQ2204ASNTR | Active | Production | SOIC (D) 16 | 2500 LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | 0 to 70 | 2204A |
| BQ2204ASNTR.B | Active | Production | SOIC (D) 16 | 2500 LARGE T&R | Yes | NIPDAU | Level-2-260C-1 YEAR | 0 to 70 | 2204A |

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

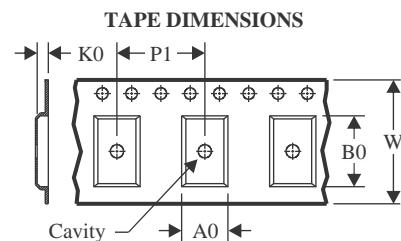
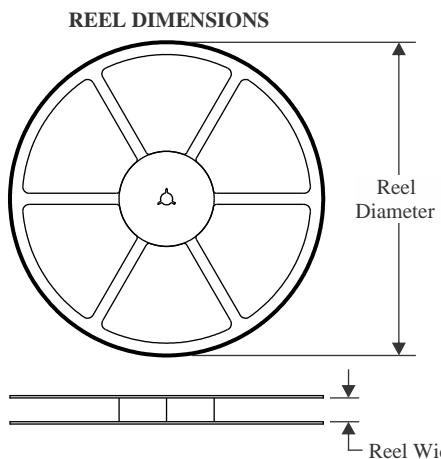
⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

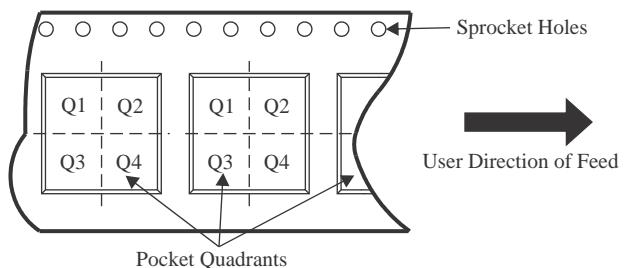
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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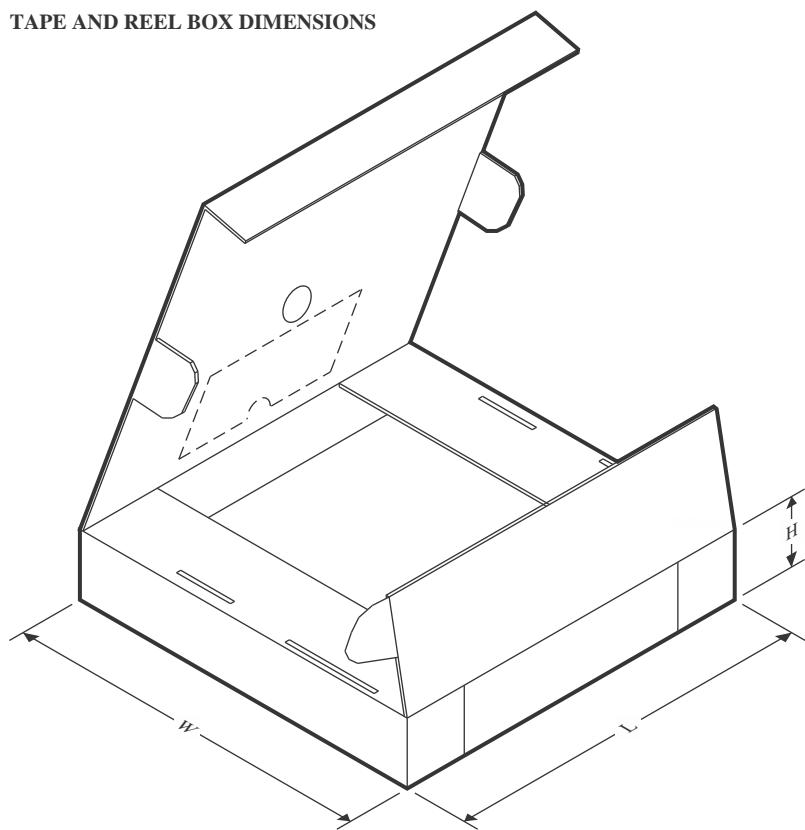
TAPE AND REEL INFORMATION


| | |
|----|---|
| A0 | Dimension designed to accommodate the component width |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


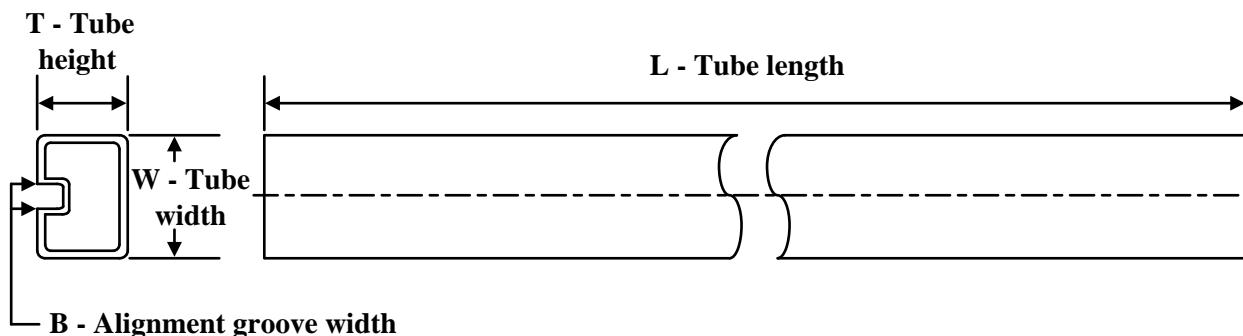
*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| BQ2204ASNTR | SOIC | D | 16 | 2500 | 330.0 | 16.4 | 6.5 | 10.3 | 2.1 | 8.0 | 16.0 | Q1 |

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|-------------|--------------|-----------------|------|------|-------------|------------|-------------|
| BQ2204ASNTR | SOIC | D | 16 | 2500 | 353.0 | 353.0 | 32.0 |

TUBE


*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (μm) | B (mm) |
|---------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| BQ2204APN | N | PDIP | 16 | 25 | 506 | 13.97 | 11230 | 4.32 |
| BQ2204APN.B | N | PDIP | 16 | 25 | 506 | 13.97 | 11230 | 4.32 |
| BQ2204ASN | D | SOIC | 16 | 40 | 506.6 | 8 | 3940 | 4.32 |
| BQ2204ASN-N | D | SOIC | 16 | 40 | 506.6 | 8 | 3940 | 4.32 |
| BQ2204ASN-N.B | D | SOIC | 16 | 40 | 506.6 | 8 | 3940 | 4.32 |
| BQ2204ASN.B | D | SOIC | 16 | 40 | 506.6 | 8 | 3940 | 4.32 |

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Last updated 10/2025